

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 7,247,900 B2  
APPLICATION NO. : 10/631858  
DATED : July 24, 2007  
INVENTOR(S) : Honma et al.

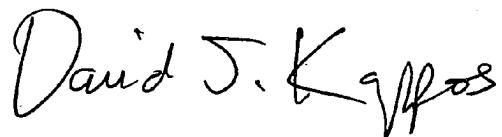
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It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page, item 56, under "References Cited" section, other References  
--Item I "Low Temperature Deposition Material"  
Section 4 "New Deposition Material"  
Ferroelectric Memory Advanced Process  
September 13, 1999-- should be added

Signed and Sealed this

Twenty-third Day of February, 2010



David J. Kappos  
*Director of the United States Patent and Trademark Office*